

20-30GHz Low Noise Amplifier

GaAs Monolithic Microwave IC

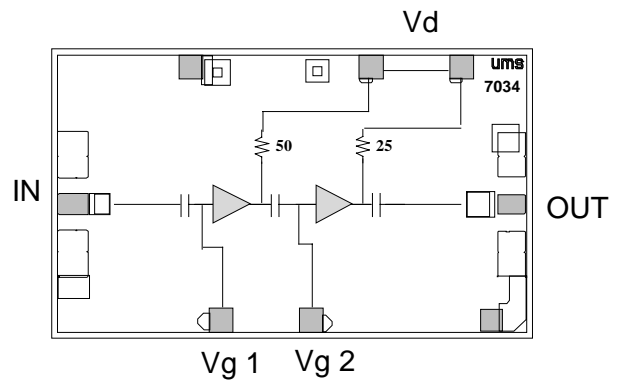
preliminary

Description

The CHA2093 is a two-stage wide band monolithic low noise amplifier.

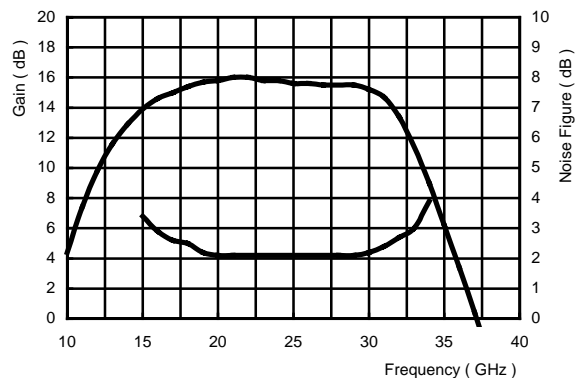
The circuit is manufactured with a standard HEMT process : 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography.

It is supplied in chip form.



Main Features

- Broad band performance 20-30GHz
- 2.2dB noise figure, 20-30GHz
- 15dB gain, ± 0.5dB gain flatness
- Low DC power consumption, 50mA
- 20dBm 3rd order intercept point
- Chip size : 1,67 x 1,03 x 0.1mm



On wafer typical measurements.

Main Characteristics

Tamb = +25°C

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------|------------------------|-----|-------|-------|------|
| NF | Noise figure, 20-30GHz | | 2.2 | 3.0 | dB |
| G | Gain | 13 | 15 | | dB |
| ΔG | Gain flatness | | ± 0.5 | ± 1.0 | dB |

ESD Protections : Electrostatic discharge sensitive device observe handling precautions !

Electrical Characteristics

Tamb = +25°C, Vd = +4V Id=45mA

| Symbol | Parameter | Min | Typ | Max | Unit |
|---------|--------------------------------------|-----|-------|-------|------|
| Fop | Operating frequency range | 20 | | 30 | Ghz |
| G | Gain (1) | 13 | 15 | | dB |
| ΔG | Gain flatness (1) | | ± 0.5 | ± 1.0 | dB |
| NF | Noise figure (1) | | 2.2 | 3.0 | dB |
| VSWRin | Input VSWR (1) | | | 3.0:1 | |
| VSWRout | Ouput VSWR (1) | | | 3.0:1 | |
| IP3 | 3rd order intercept point | | 20 | | dBm |
| P1dB | Output power at 1dB gain compression | | 13 | | dBm |
| Id | Drain bias current | | 50 | | mA |

(1) These values are representative of on-wafer measurements that are made without bonding wires at the RF ports. When the chip is attached with typical 0.15nH input and output bonding wires , the indicated parameter values should be improved.

Absolute Maximum Ratings (1)

Tamb = +25°C

| Symbol | Parameter | Values | Unit |
|--------|--|-------------|------|
| Vd | Drain bias voltage | 4.0 | V |
| Pin | Maximum peak input power overdrive (2) | +15 | dBm |
| Top | Operating temperature range | -40 to +85 | °C |
| Tstg | Storage temperature range | -55 to +125 | °C |

(1) Operation of this device above anyone of these paramaters may cause permanent damage.

(2) Duration < 1s.

Typical Results

Chip Typical Response (On wafer Sij) :

Tamb = +25°C

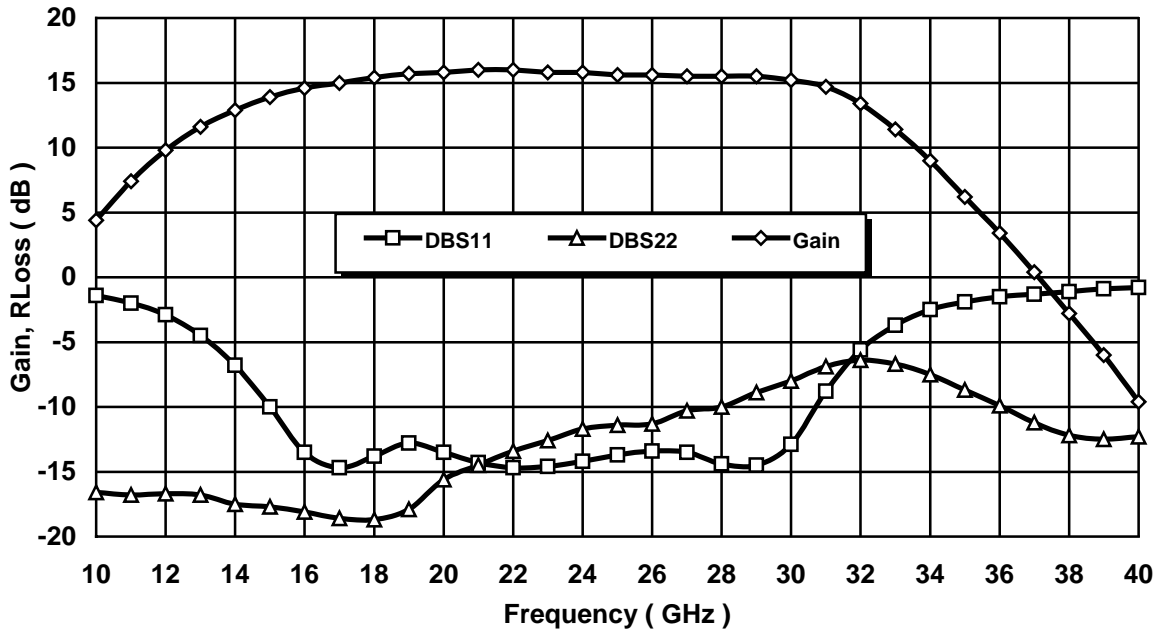
Bias Conditions : Vd = +4V Id=45mA

| Freq GHz | MS11 dB | PS11 ° | MS12 dB | PS12 ° | MS21 dB | PS21 ° | MS22 dB | PS22 ° |
|-------------|------------|-----------|------------|-----------|------------|-----------|------------|-----------|
| 10 | -1.36 | 140 | -62.29 | -138.5 | 4.35 | 51.6 | -16.6 | 151.6 |
| 11 | -1.98 | 121.9 | -58.39 | -130.1 | 7.36 | 27.2 | -16.75 | 145.1 |
| 12 | -2.93 | 101.1 | -53.05 | -130.3 | 9.77 | 0.8 | -16.67 | 137.9 |
| 13 | -4.5 | 77.7 | -49.08 | -146.8 | 11.61 | -26.2 | -16.77 | 129.8 |
| 14 | -6.8 | 50.1 | -46.97 | -163.9 | 12.9 | -53.2 | -17.47 | 122.7 |
| 15 | -10.02 | 16.4 | -44.52 | 173.2 | 13.86 | -78.7 | -17.67 | 122.2 |
| 16 | -13.47 | -30 | -42.23 | 160.2 | 14.55 | -103.5 | -18.06 | 118.4 |
| 17 | -14.68 | -86 | -40.43 | 138.2 | 15 | -127 | -18.55 | 118.4 |
| 18 | -13.76 | -131 | -39.41 | 126.2 | 15.36 | -149.8 | -18.7 | 125.4 |
| 19 | -12.83 | -159.2 | -38 | 104.7 | 15.69 | -171.8 | -17.9 | 131.3 |
| 20 | -13.51 | 177.8 | -36.01 | 92.4 | 15.79 | 165.6 | -15.62 | 131.1 |
| 21 | -14.3 | 170.9 | -34.99 | 63.7 | 15.96 | 144.3 | -14.48 | 127 |
| 22 | -14.74 | 167.2 | -34.53 | 46.8 | 15.98 | 122.3 | -13.4 | 120.5 |
| 23 | -14.63 | 168 | -34.46 | 24.6 | 15.84 | 102.1 | -12.6 | 116.3 |
| 24 | -14.15 | 163.4 | -33.67 | 6.3 | 15.75 | 80.9 | -11.67 | 107.1 |
| 25 | -13.71 | 155.8 | -33.27 | -7.6 | 15.6 | 60.2 | -11.4 | 100.6 |
| 26 | -13.42 | 145.5 | -32.65 | -29.3 | 15.55 | 40.3 | -11.3 | 96.1 |
| 27 | -13.54 | 124.4 | -32.6 | -51.5 | 15.46 | 18.6 | -10.33 | 91.6 |
| 28 | -14.43 | 100.2 | -32.49 | -68.3 | 15.48 | -2.8 | -9.98 | 85.7 |
| 29 | -14.48 | 56.9 | -31.69 | -88.8 | 15.48 | -27.3 | -8.88 | 80.2 |
| 30 | -12.87 | 5.6 | -31.87 | -115.7 | 15.24 | -53 | -7.99 | 70.5 |
| 31 | -8.84 | -37.4 | -31.22 | -140.4 | 14.69 | -82.2 | -6.86 | 58.1 |
| 32 | -5.55 | -73.3 | -31.23 | -171 | 13.43 | -112.8 | -6.35 | 40.1 |
| 33 | -3.72 | -101.3 | -32.96 | 159.7 | 11.43 | -141.9 | -6.69 | 20.4 |
| 34 | -2.5 | -123.2 | -34.73 | 134.8 | 9.01 | -168.7 | -7.51 | 1.5 |
| 35 | -1.88 | -141.2 | -35.69 | 121.6 | 6.2 | 167.5 | -8.65 | -17 |
| 36 | -1.52 | -155.7 | -35.69 | 98 | 3.35 | 145.9 | -9.92 | -36.6 |
| 37 | -1.32 | -167.5 | -37.95 | 72.2 | 0.36 | 125.7 | -11.17 | -56.5 |
| 38 | -1.07 | -177.6 | -38.15 | 56.8 | -2.78 | 107.4 | -12.15 | -78.9 |
| 39 | -0.93 | 172.6 | -43.41 | 86.9 | -6.02 | 89 | -12.5 | -103.1 |
| 40 | -0.82 | 164.7 | -43.1 | 76.9 | -9.59 | 71.9 | -12.27 | -127.3 |
| 41 | -0.68 | 157.2 | -43.1 | 44.4 | -13.6 | 55.3 | -11.82 | -148.5 |
| 42 | -0.52 | 149.5 | -43.23 | 39.6 | -18.24 | 40.2 | -10.89 | -166.3 |
| 43 | -0.5 | 142 | -44.08 | 24 | -24.6 | 27.2 | -9.87 | -179.6 |
| 44 | -0.41 | 135.3 | -45.8 | 21 | -35.19 | 30.1 | -8.91 | 167.4 |
| 45 | -0.37 | 128.4 | -45.05 | 18.1 | -37.14 | 126.8 | -8.04 | 156.2 |

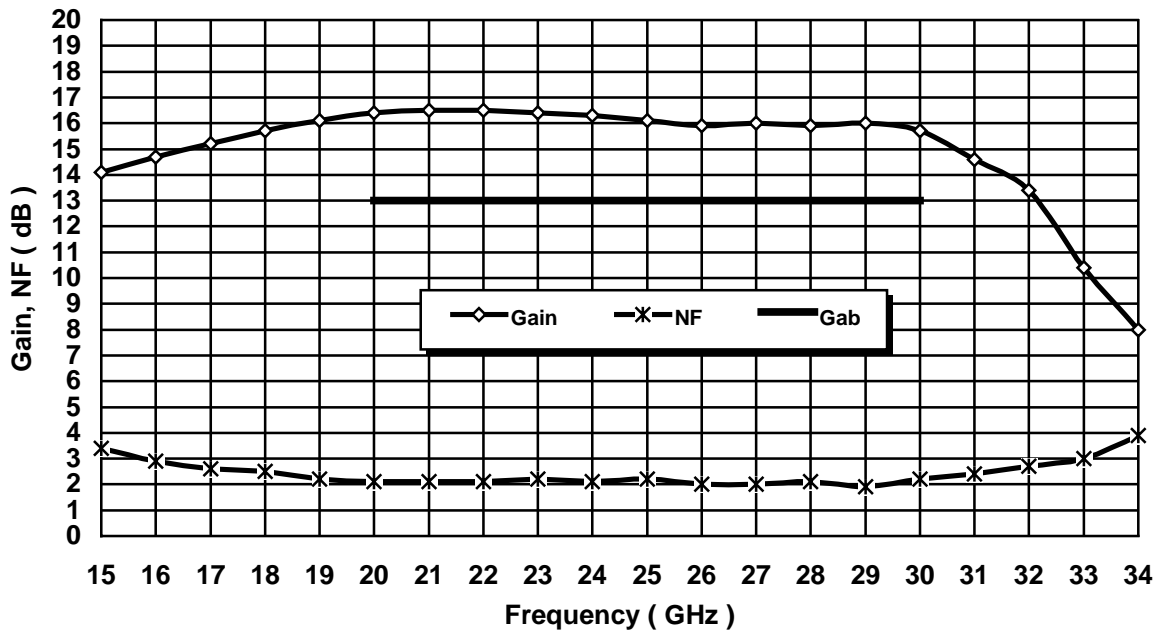
Typical Results

Chip Typical Response (On wafer Sij) :

Tamb = +25°C
 Vd = 4V ; Id = 45mA



Typical Gain and Matching measurements on wafer.

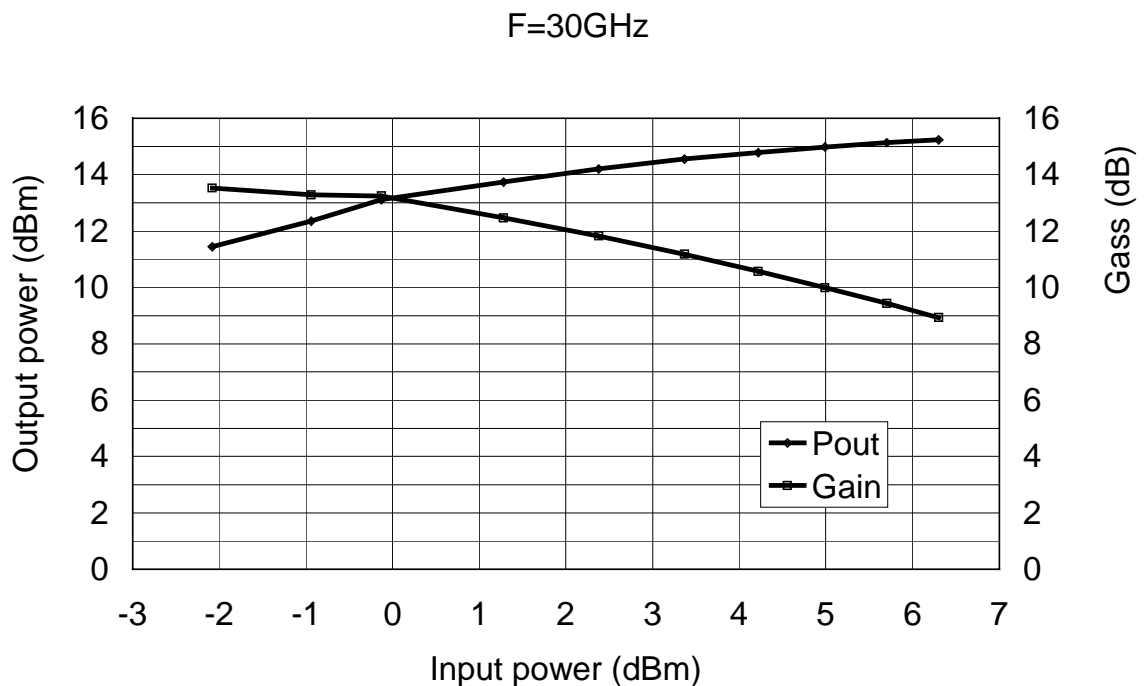
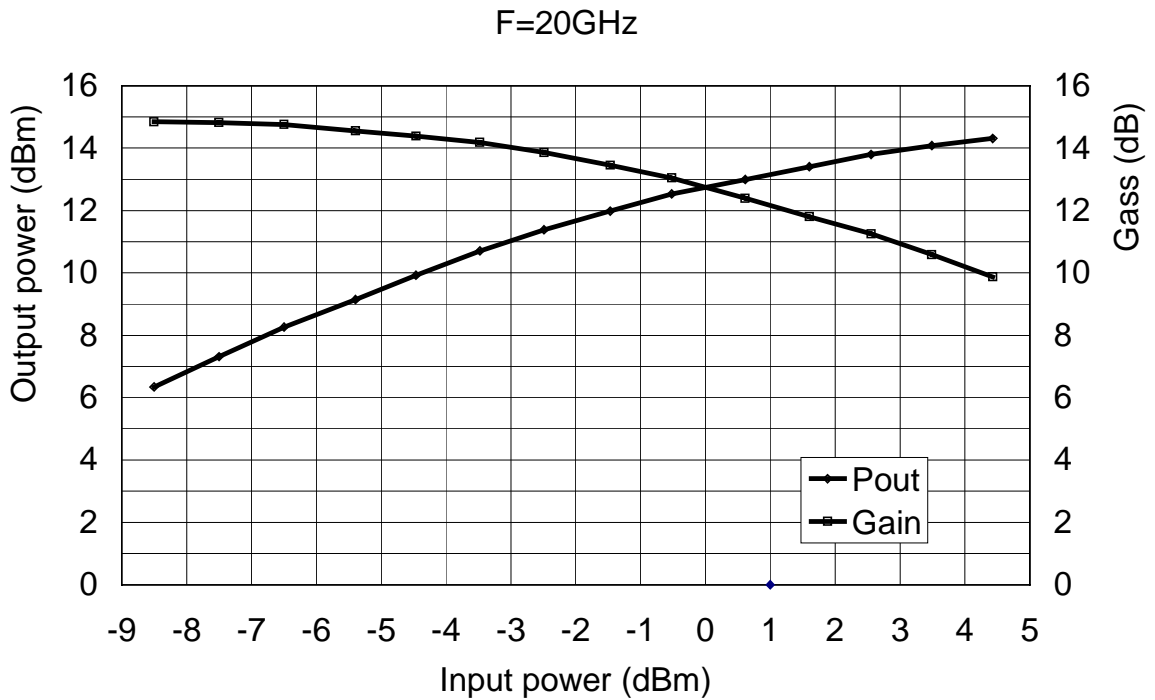


Typical Gain and Noise Figure measurements on wafer.

Typical Results

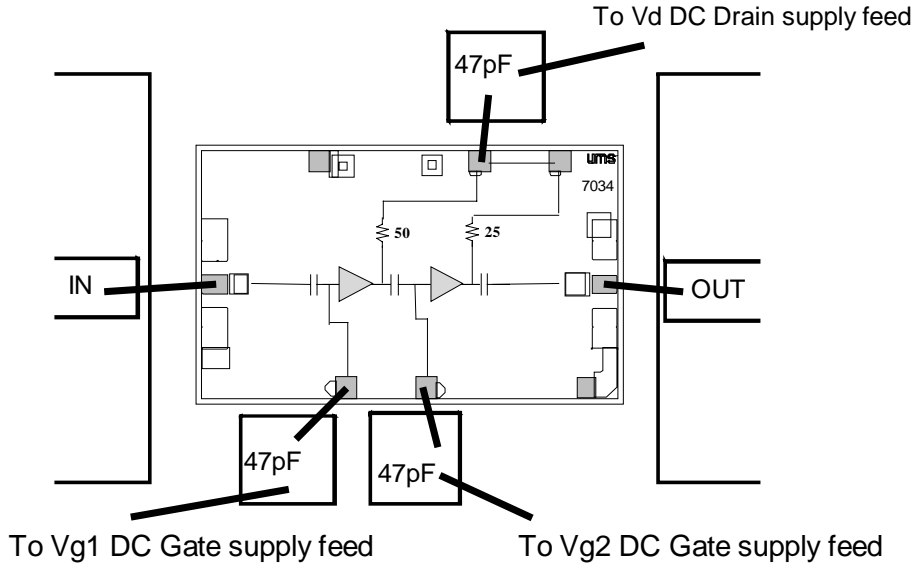
Tamb = +25°C

Vd = 4V ; Id = 45mA



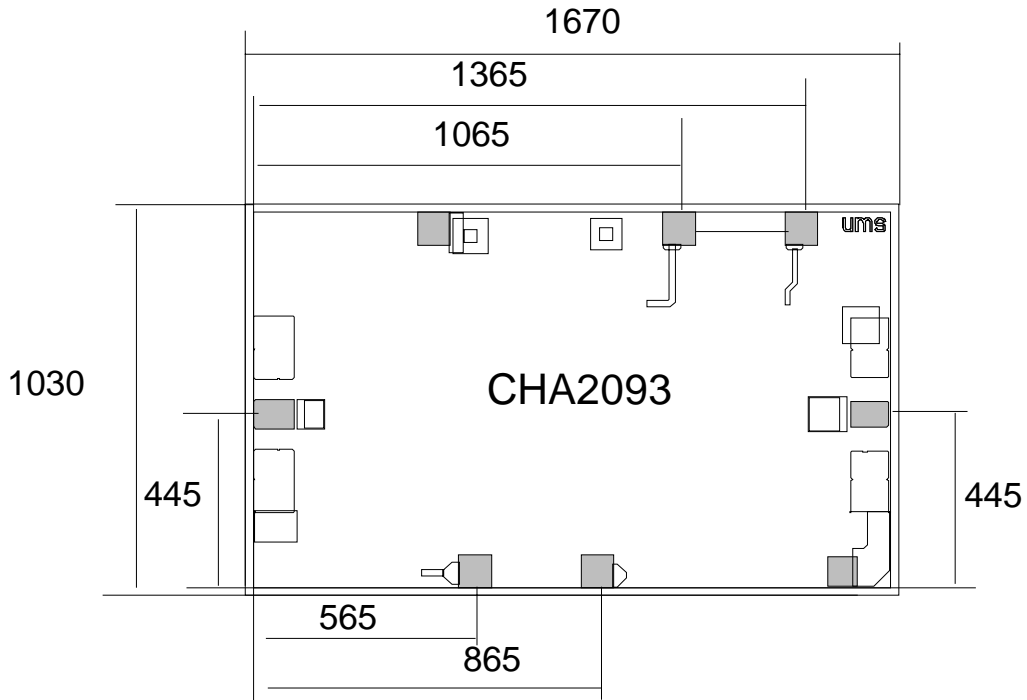
**Typical Output Power and Gain measurements in test jig
(included losses of the jig)**

Typical Chip Assembly



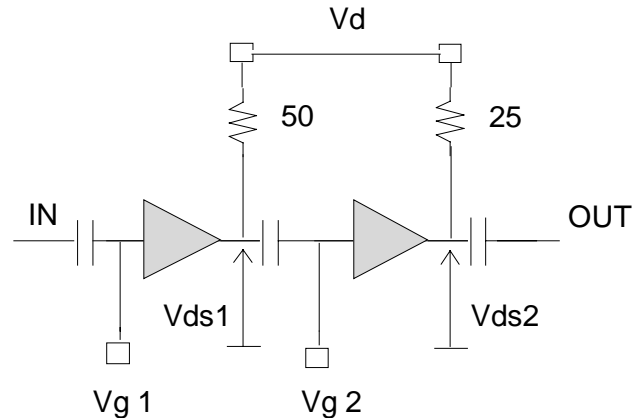
Dimensions : 1670 x 1030µm ± 10µm

Mechanical data



Chip Biasing

This chip is a two stage amplifier, and flexibility is provided by the access to number of pads. The internal DC electrical schematic is given in order to use these pads in a safe way.



The two requirements are :

- N°1 : Not exceed $V_{ds} = 3.5\text{V}$ (internal Drain to Source voltage).
- N°2 : Not biased in such a way that V_{gs} becomes positive.
(internal Gate to Source voltage)

We propose two standard biasing :

Low Noise and low consumption : $V_d = 3.5\text{V}$ and $I_d = 30\text{mA}$ ($V_{g1}=V_{g2}$)

Low Noise and high output power : $V_d = 4.0\text{V}$ and $I_d = 45\text{mA}$. (A separate acces to the gate voltages of the first and the output stage is provided. Nominal bias is obtained for a typical current of 30mA for the output stage and 15 mA for the first stage. The first step to bias the amplifier is to tune the $V_{g1} = -1\text{V}$ and V_{g2} to drive 30mA for the full amplifier. Then V_{g1} is reduced to obtain 45 mA of current through the amplifier.

Ordering Information

Chip form : CHA2093-99F/00

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